

Silicon PNP Power Transistors

NS50P

DESCRIPTION

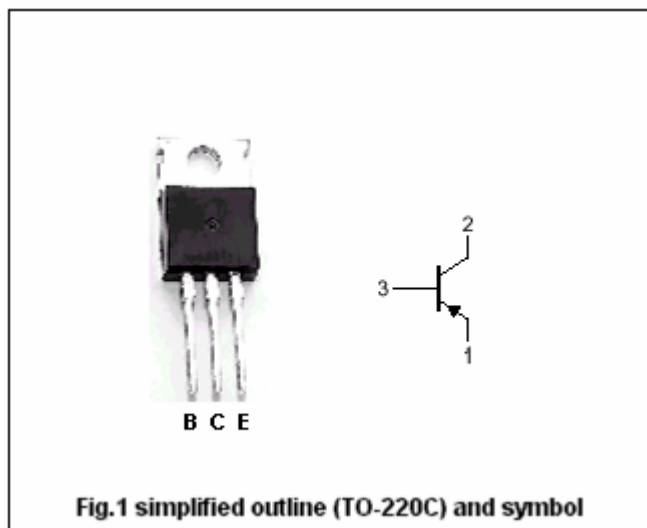
- With TO-220C package
- Complement to type NS50N

APPLICATIONS

- For medium power linear amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

ABSOLUTE MAXIMUM RATINGS($T_C=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-60	V
V_{CEO}	Collector-emitter voltage	Open base	-60	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current (DC)		-6	A
I_{CM}	Collector current-Pulse		-10	A
I_B	Base current		-2	A
P_C	Collector power dissipation	$T_C=25^{\circ}\text{C}$	65	W
		$T_a=25^{\circ}\text{C}$	2	
T_j	Junction temperature		150	$^{\circ}\text{C}$
T_{stg}	Storage temperature		-65~150	$^{\circ}\text{C}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	I _C =-30mA; I _B =0	-60			V
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =-6A ; I _B =-0.6A			-1.5	V
V _{BE}	Base-emitter on voltage	I _C =-6A ; V _{CE} =-4V			-2.0	V
I _{CES}	Collector cut-off current	V _{CE} =-60V; V _{EB} =0			-0.4	mA
I _{CEO}	Collector cut-off current	V _{CE} =-30V; I _B =0			-0.7	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-1.0	mA
h _{FE-1}	DC current gain	I _C =-0.3A ; V _{CE} =-4V	50		160	
h _{FE-2}	DC current gain	I _C =-3A ; V _{CE} =-4V	15			
f _T	Transition frequency	I _C =-0.5A ; V _{CE} =-10V	3			MHz

◆ h_{FE-1} Classifications

A	B
50-100	80-160

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PACKAGE OUTLINE

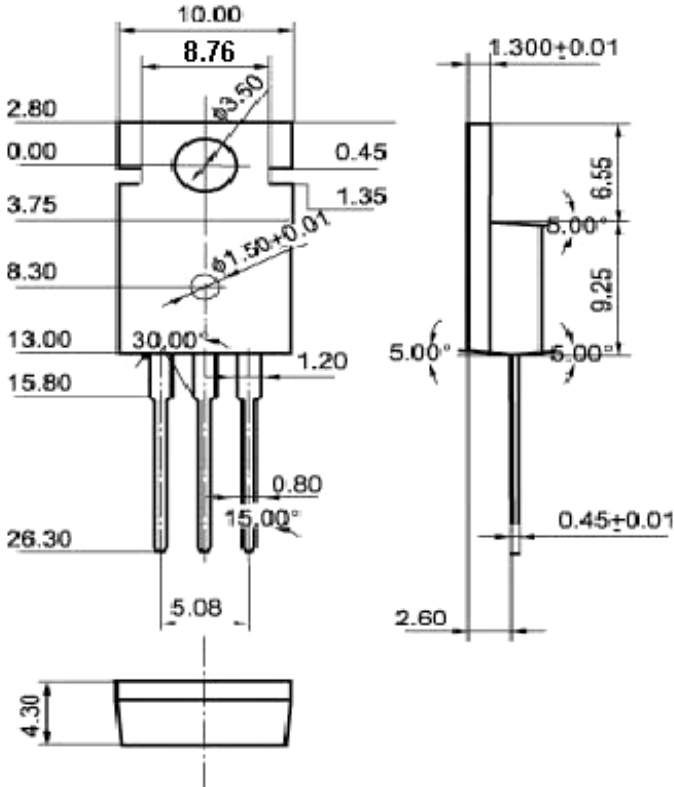


Fig.2 Outline dimensions